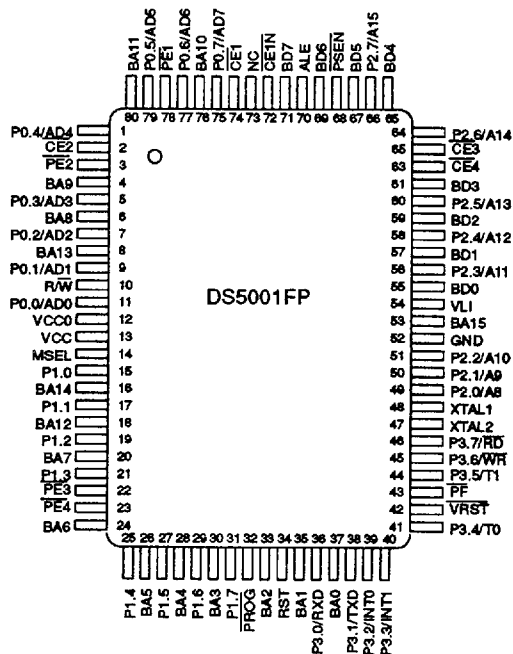


DALLAS SEMICONDUCTOR CORP

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SEMICONDUCTOR**DS5001FP**
128K Soft Micro Chip**FEATURES**

- 8051 compatible uC adapts to its task
 - Accesses up to 128K bytes of nonvolatile SRAM
 - In-system programming via on-chip serial port
 - Can modify its own program or data memory
 - Accesses memory on a separate Byte-wide bus
 - Performs CRC-16 check of NVRAM memory
 - Decodes memory and peripheral chip enables
- Crashproof Operation
 - Maintains all nonvolatile resources for over 10 years
 - Power-fail Reset
 - Early Warning Power-fail Interrupt
 - Watchdog Timer
 - Lithium backs user SRAM for program/data storage
 - Precision band-gap reference for power monitor
- Fully 8051 Compatible
 - 128 bytes scratchpad RAM
 - Two timer/counters
 - On-chip serial port
 - 32 parallel I/O port pins
- Software Security Available (DS5002FP)

PIN ASSIGNMENT**DESCRIPTION**

The DS5001FP is an 8051 compatible microcontroller based on nonvolatile RAM technology. It is designed for systems that need large quantities of nonvolatile memory. Like its predecessor the DS5000, the DS5001FP is substantially more flexible than a standard 8051. It provides full compatibility with the 8051 instruction set, timers, serial port, and parallel I/O ports. By using NVRAM instead of ROM, the user can pro-

gram, then reprogram the microcontroller while in-system. The application software can even change its own operation. This allows frequent software upgrades, adaptive programs, customized systems, etc. In addition, by using NVSRAM, the DS5001FP is ideal for data logging applications. It also connects easily to a Dallas Real-time Clock for time stamp and date.

The DS5001FP provides the benefits of NVRAM without using I/O resources. It uses a non-multiplexed Byte-wide address and data bus for memory access. This bus can perform all memory access and provides decoded chip enables for SRAM. This leaves the 32 I/O port pins free for application use. The DS5001FP uses ordinary SRAM and battery backs the memory contents with an user's external lithium cell. Data is maintained for over 10 years with a very small lithium cell. A DS5001FP also provides crashproof operation in portable systems or systems with unreliable power. These features include the ability to save the operating state, Power-fail Reset, Power-fail Interrupt, and Watchdog Timer.

A user loads programs into the DS5001FP via its on-chip Serial Bootstrap Loader. This function supervises the loading of software into NVRAM, validates it, then becomes transparent to the user. Software can be stored in multiple 32K or one 128K byte CMOS SRAM(s). Using its internal Partitioning, the DS5001FP can divide a common RAM into user selectable program and data segments. This Partition can be selected at program loading time, but can be modified anytime later. The micro will decode memory access to the SRAM, access memory via its Byte-wide bus and write-protect the memory portion designated as ROM. Combining program and data storage in one device saves board space and cost.

The DS5001FP offers several bank switches for access to even more memory. In addition to the primary data

area of 64K bytes, a peripheral selector creates a second 64K byte data space with four accompanying chip enables. This area can be used for memory mapped peripherals or more data storage. The DS5001FP can also use its Expanded bus on Ports 0 and 2 (like an 8051) to access an additional 64K bytes of data space. Lastly, the DS5001FP provides one additional bank switch that changes up to 60K bytes of the NVRAM program space into data memory. Thus with a small amount of logic, the DS5001 accesses up to 252K bytes of data memory.

For a user that wants a pre-constructed module using the DS5001FP, RAM, lithium cell, and optional clock; the DS2251(T) is available and described in separate data sheet. More details are also contained in the User's Guide section of the Soft Microcontroller Data Book. For users that desire software security, the DS5002FP is functionally identical to the DS5001FP but provides the best firmware security available.

ORDERING INFORMATION

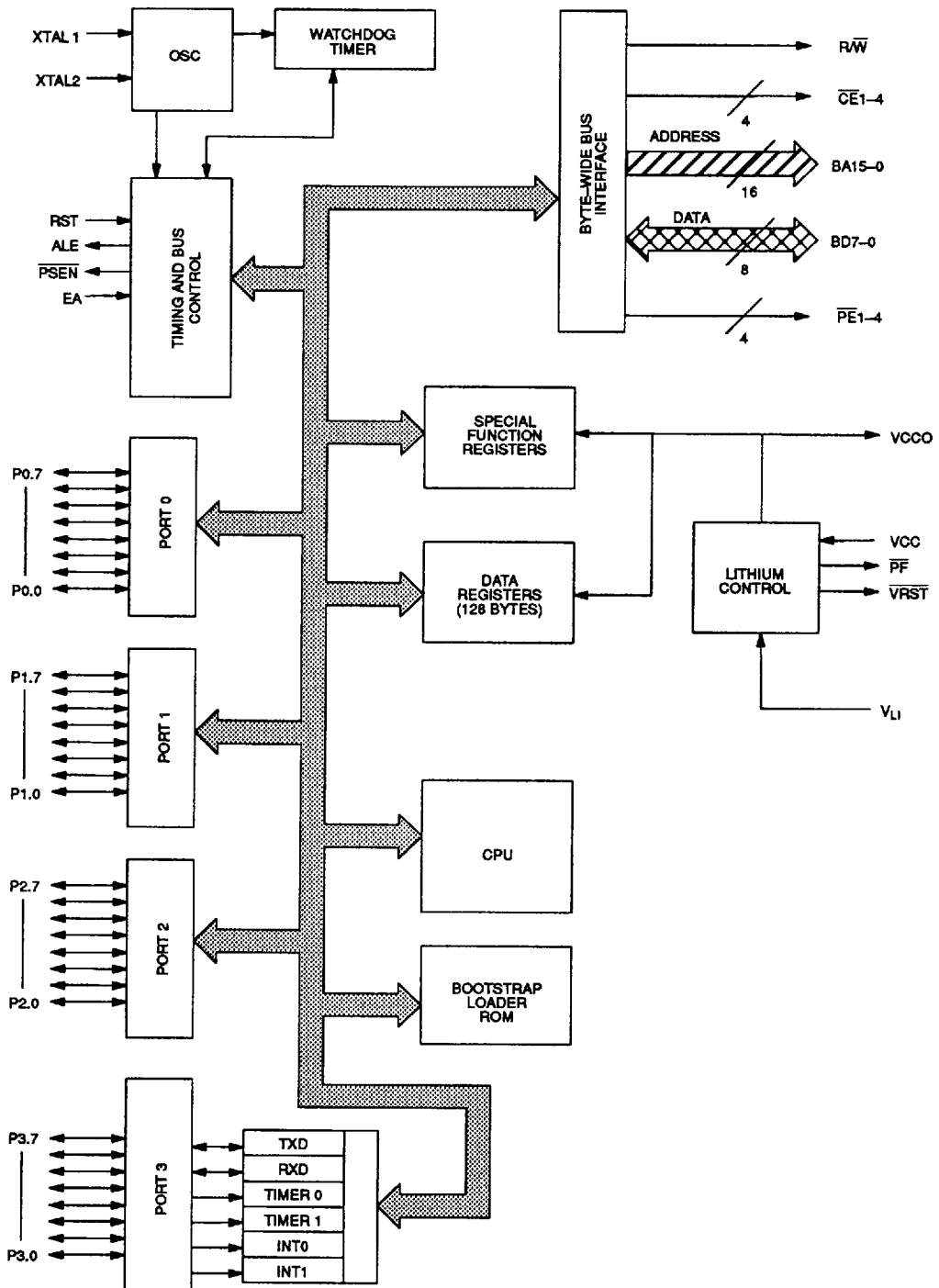
Part Number	Max. Crystal Speed
DS5001FP-12	12 MHz
DS5001FP-16	16 MHz

Operating information is contained in the User's Guide section of the Soft Microcontroller Data Book. This data sheet provides ordering information, pin-out, and electrical specifications.

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DS5001FP BLOCK DIAGRAM Figure 1

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PIN DESCRIPTION

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PIN NUMBER	DESCRIPTION
11, 9, 7, 5, 1, 79, 77, 75	P0.0–P0.7 General purpose I/O Port 0. This port is open–drain and can not drive a logic 1. It requires external pull–ups. Port 0 is also the multiplexed Expanded Address/Data bus. When used in this mode, it does not require pull–ups.
15, 17, 19, 21, 25, 27, 29, 31	P1.0–P1.7 General purpose I/O Port 1.
49, 50, 51, 56, 58, 60, 64, 66	P2.0–P2.7 General purpose I/O Port 2. Also serves as the MSB of the address in expanded memory accesses, and as pins of the RPC mode when used.
36	P3.0 RXD General purpose I/O port pin 3.0. Also serves as the receive signal for the on board UART. This pin should <u>NOT</u> be connected directly to a PC COM port.
38	P3.1 TXD General purpose I/O port pin 3.1. Also serves as the transmit signal for the on board UART. This pin should <u>NOT</u> be connected directly to a PC COM port.
39	P3.2 $\overline{\text{INT0}}$ General purpose I/O port pin 3.2. Also serves as the active low External Interrupt 0.
40	P3.3 $\overline{\text{INT1}}$ General purpose I/O port pin 3.3. Also serves as the active low External Interrupt 1.
41	P3.4 T0 General purpose I/O port pin 3.4. Also serves as the Timer 0 input.
44	P3.5 T1 General purpose I/O port pin 3.5. Also serves as the Timer 1 input.
45	P3.6 $\overline{\text{WR}}$ General purpose I/O port pin. Also serves as the write strobe for Expanded bus operation.
46	P3.7 $\overline{\text{RD}}$ General purpose I/O port pin. Also serves as the read strobe for Expanded bus operation.
34	RST Active high reset input. A logic 1 applied to this pin will activate a reset state. This pin is pulled down internally so this pin can be left unconnected if not used. An RC power–on reset circuit is not needed and is <u>NOT</u> recommended.
68	PSEN Program Store Enable. This active low signal is used to enable an external program memory when using the Expanded bus. It is normally an output and should be unconnected if not used. $\overline{\text{PSEN}}$ also is used to invoke the Bootstrap Loader. At this time, $\overline{\text{PSEN}}$ will be pulled down externally. This should only be done once the DS5001FP is already in a reset state. The device that pulls down should be open drain since it must not interfere with $\overline{\text{PSEN}}$ under normal operation.
70	ALE Address Latch Enable. Used to de–multiplex the multiplexed Expanded Address/Data bus on Port 0. This pin is normally connected to the clock input on a '373 type transparent latch.

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PIN NUMBER	DESCRIPTION
47, 48	XTAL2, XTAL1 Used to connect an external crystal to the internal oscillator. XTAL1 is the input to an inverting amplifier and XTAL2 is the output.
52	GND Logic ground.
13	V _{CC} +5V
12	V _{CCO} V _{CC} Output. This is switched between V _{CC} and V _{LI} by internal circuits based on the level of V _{CC} . When power is above the lithium input, power will be drawn from V _{CC} . The lithium cell remains isolated from a load. When V _{CC} is below V _{LI} , the V _{CCO} switches to the V _{LI} source. V _{CCO} should be connected to the V _{CC} pin of an SRAM.
54	V _{LI} Lithium Voltage Input. Connect to a lithium cell greater than V _{LImin} and no greater than V _{LImax} as shown in the electrical specifications. Nominal value is +3V.
53, 16, 8, 18, 80, 76, 4, 6, 20, 24, 26, 28, 30, 33, 35, 37	BA15-0 Byte-wide Address bus bits 15-0. This bus is combined with the non-multiplexed data bus (BD7-0) to access NVSRAM. Decoding is performed using CE1 through CE4. Therefore, BA15 is not actually needed except for monitoring and debugging. Read/write access is controlled by R/W. BA14-0 connect directly to an 8K, 32K, or 128K SRAM. If an 8K RAM is used, BA13 and BA14 will be unconnected. If a 128K SRAM is used, the micro converts CE2 and CE3 to serve as A16 and A15 respectively.
71, 69, 67, 65, 61, 59, 57, 55	BD7-0 Byte-wide Data bus bits 7-0. This 8 bit bi-directional bus is combined with the non-multiplexed address bus (BA14-0) to access NVSRAM. BD7-0 connect directly to an SRAM, and optionally to a Real-time Clock or other peripheral.
10	R/W Read/Write. This signal provides the write enable to the SRAMs on the Byte-wide bus. It is controlled by the memory map and Partition. The blocks selected as Program (ROM) will be write protected.
74	CE1 Chip Enable 1. This is the primary decoded chip enable for memory access on the Byte-wide bus. It connects to the chip enable input of one SRAM. CE1 is lithium backed. It will remain in a logic high inactive state when V _{CC} falls below V _{LI} .
72	CE1N Non battery backed version of chip enable 1. This can be used with a 32K byte EPROM. It should not be used with a battery backed chip.
2	CE2 Chip Enable 2. This chip enable is provided to access a second 32K block of memory. It connects to the chip enable input of one SRAM. When MSEL=0, the micro converts CE2 into A16 for a 128K x 8 SRAM. CE2 is lithium backed and will remain at a logic high when V _{CC} falls below V _{LI} .
63	CE3 Chip Enable 3. This chip enable is provided to access a third 32K block of memory. It connects to the chip enable input of one SRAM. When MSEL=0, the micro converts CE3 into A15 for a 128K x 8 SRAM. CE3 is lithium backed and will remain at a logic high when V _{CC} falls below V _{LI} .

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PIN NUMBER	DESCRIPTION
62	CE4 Chip Enable 4. This chip enable is provided to access a fourth 32K block of memory. It connects to the chip enable input of one SRAM. When MSEL=0, this signal is unused. CE4 is lithium backed and will remain at a logic high when V _{CC} falls below V _{LI} .
78	PE1 Peripheral Enable 1. Accesses data memory between addresses 0000h and 3FFFh when the PES bit is set to a logic 1. Commonly used to chip enable a Byte-wide real-time Clock such as the DS1283. PE1 is lithium backed and will remain at a logic high when V _{CC} falls below V _{LI} . Connect PE1 to battery backed functions only.
3	PE2 Peripheral Enable 2. Accesses data memory between addresses 4000h and 7FFFh when the PES bit is set to a logic 1. PE2 is lithium backed and will remain at a logic high when V _{CC} falls below V _{LI} . Connect PE2 to battery backed functions only.
22	PE3 Peripheral Enable 3. Accesses data memory between addresses 8000h and BFFFh when the PES bit is set to a logic 1. PE3 is not lithium backed and can be connected to any type of peripheral function. If connected to a battery backed chip, it will need additional circuitry to maintain the chip enable in an inactive state when V _{CC} < V _{LI} .
23	PE4 Peripheral Enable 4. Accesses data memory between addresses C000h and FFFFh when the PES bit is set to a logic 1. PE4 is not lithium backed and can be connected to any type of peripheral function. If connected to a battery backed chip, it will need additional circuitry to maintain the chip enable in an inactive state when V _{CC} < V _{LI} .
32	PROG Invokes the Bootstrap loader on a falling edge. This signal should be debounced so that only one edge is detected. If connected to ground, the micro will enter Bootstrap loading on power up. This signal is pulled up internally.
42	VRST This I/O pin indicates that the power supply (V _{CC}) has fallen below the V _{CCmin} level and the micro is in a reset state. When this occurs, the DS5001FP will drive this pin to a logic 0. Because the micro is lithium backed, this signal is guaranteed even when V _{CC} =0V. Because it is an I/O pin, it will also force a reset if pulled low externally. This allows multiple parts to synchronize their power-down resets.
43	PF This output goes to a logic 0 to indicate that the micro has switched to lithium backup. This corresponds to V _{CC} < V _{LI} . Because the micro is lithium backed, this signal is guaranteed even when V _{CC} =0V. The normal application of this signal is to control lithium powered current to isolate battery backed functions from non-battery backed functions.
14	MSEL Memory select. This signal controls the memory size selection. When MSEL= +5V, the DS5001FP expects to use 32K x 8 SRAMs. When MSEL = 0V, the DS5001FP expects to use a 128K x 8 SRAM. MSEL must be connected regardless of Partition, Mode, etc.
73	NC Do not connect.

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INSTRUCTION SET

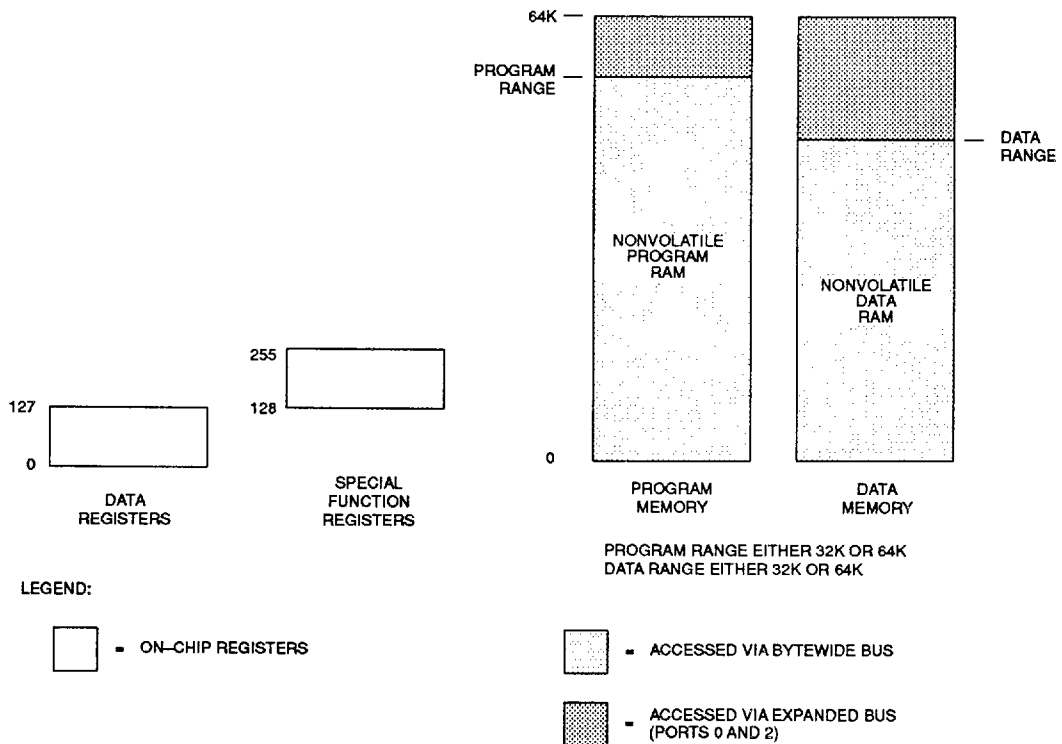
The DS5001FP executes an instruction set that is object code compatible with the industry standard 8051 microcontroller. As a result, software development packages such as assemblers and compilers that have been written for the 8051 are compatible with the DS5001FP. A complete description of the instruction set and operation are provided in the User's Guide section of the Soft Microcontroller Data Book.

Also note that the DS5001FP is embodied in the DS2251(T) module. The DS2251(T) combines the DS5001FP with between 32K and 128K of SRAM, and a lithium cell. An optional Real-time Clock is also available in the DS2251T. This is packaged in a 72-pin SIMM module.

MEMORY ORGANIZATION

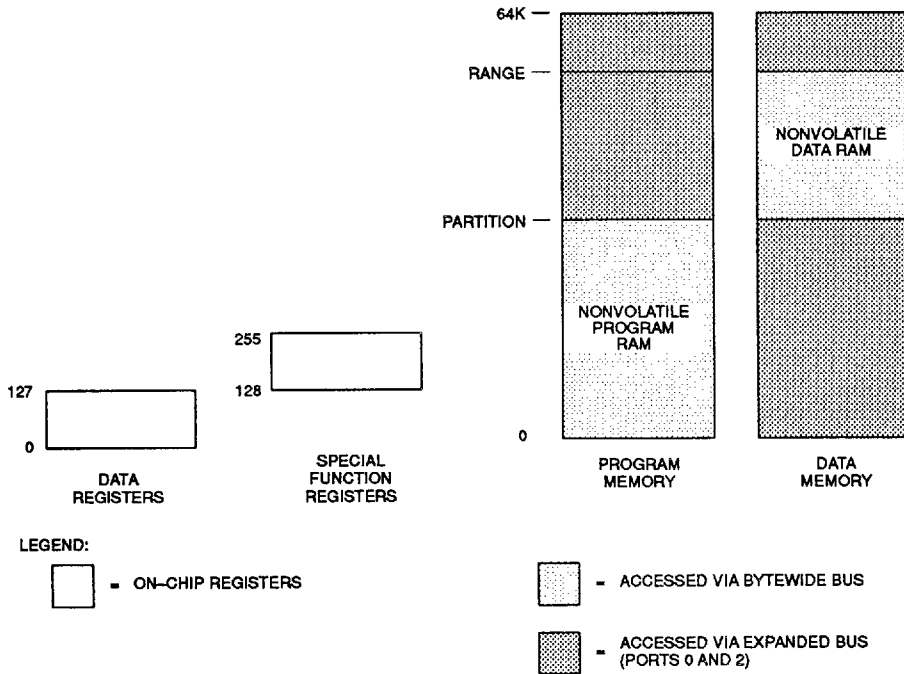
Figure 2 illustrates the memory map accessed by the DS5001FP. The entire 64K of program and 64K of data are potentially available to the Byte-wide bus. This preserves the I/O ports for application use. The user controls the portion of memory that is actually mapped to the Byte-wide bus by selecting the Program Range and Data Range. Any area not mapped into the NVRAM is reached via the Expanded bus on Ports 0 and 2. An alternate configuration allows dynamic Partitioning of a 64K space as shown in Figure 3. Selecting PES=1 provides another 64K of potential data storage or memory mapped peripheral space as shown in Figure 4. These selections are made using Special Function Registers. The memory map and its controls are covered in detail in the User's Guide section of the Soft Microcontroller Data Book.

MEMORY MAP OF THE DS5001FP WITH PM=1 Figure 2

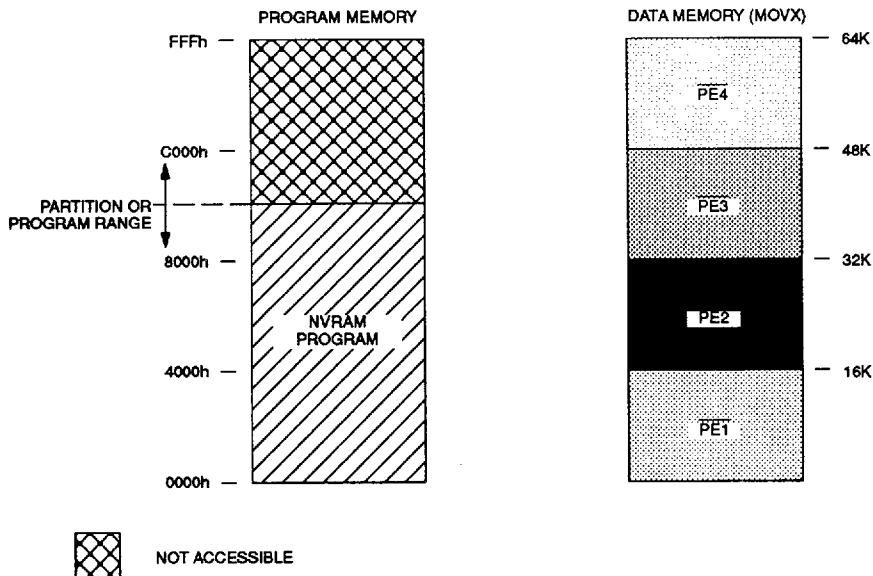


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MEMORY MAP OF THE DS5001FP WITH PM=0 Figure 3



MEMORY MAP OF THE DS5001FP WITH PES=1 Figure 4

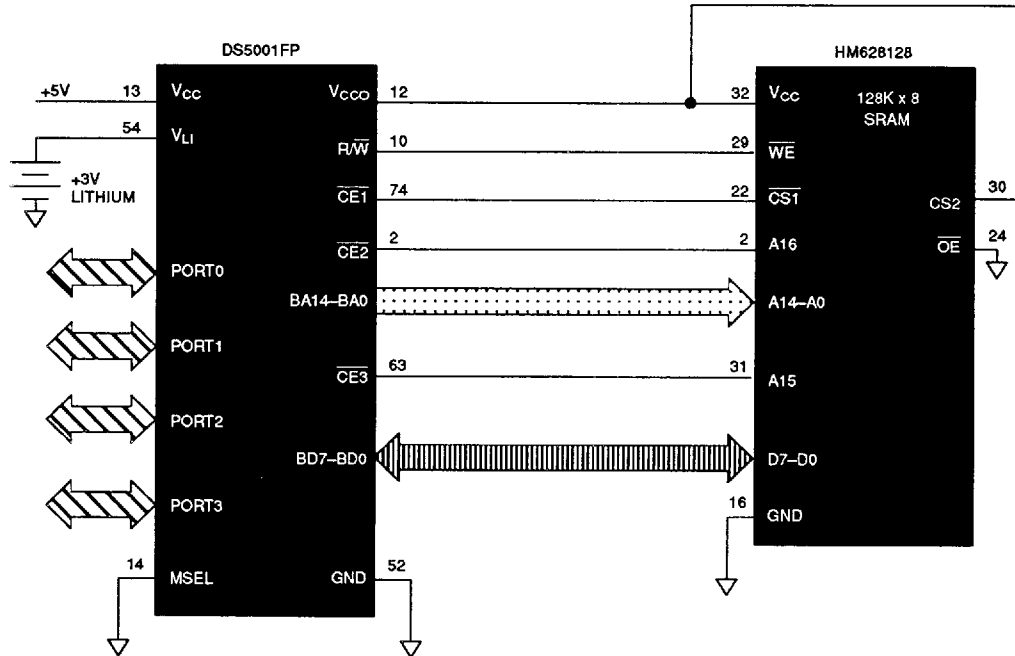


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Figure 5 illustrates a typical memory connection for a system using a 128K byte SRAM. Note that in this configuration, both program and data are stored in a common RAM chip Figure 6 shows a similar system with

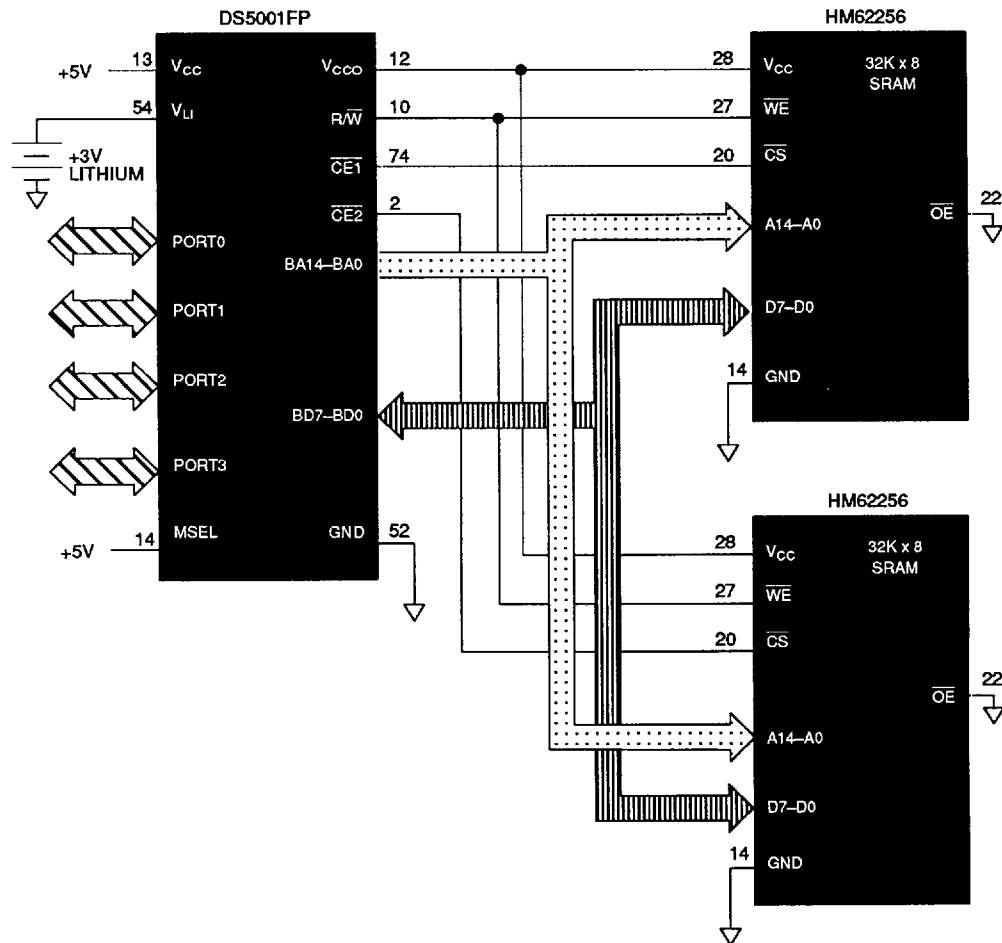
using two 32K byte SRAMs. The Byte-wide Address bus connects to the SRAM address lines. The bi-directional Byte-wide data bus connects the data I/O lines of the SRAM.

DS5001FP CONNECTION TO 128K X 8 SRAM Figure 5



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DS5001FP CONNECTION TO 64K X 8 SRAM Figure 6

**POWER MANAGEMENT**

The DS5001FP monitors V_{CC} to provide Power-fail Reset, early warning Power-fail Interrupt, and switch over to lithium backup. It uses an internal band-gap reference in determining the switch points. These are called V_{PFW} , V_{CCMIN} , and V_{LI} respectively. When V_{CC} drops below V_{PFW} , the DS5001FP will perform an interrupt vector to location 2Bh if the power fail warning was enabled. Full processor operation continues regardless. When power falls further to V_{CCMIN} , the DS5001FP invokes a reset state. No further code execution will be performed unless power rises back above V_{CCMIN} . All decoded chip enables and the R/W signal go to an inactive (logic 1) state. V_{CC} is still the power source at this time. When V_{CC} drops further to

below V_{LI} , internal circuitry will switch to the lithium cell for power. The majority of internal circuits will be disabled and the remaining nonvolatile states will be retained. Any devices connected to V_{CCO} will be powered by the lithium cell at this time. V_{CCO} will be at the lithium battery voltage less a diode drop. This drop will vary depending on the load. Low power SRAMs should be used for this reason. When using the DS5001FP, the user must select the appropriate battery to match the RAM data retention current and the desired backup lifetime. Note that the lithium cell is only loaded when $V_{CC} < V_{LI}$. The User's Guide has more information on this topic. The trip points V_{CCMIN} and V_{PFW} are listed in the electrical specifications.

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ABSOLUTE MAXIMUM RATINGS*

Voltage on Any Pin Relative to Ground	-0.3V to 7.0V
Operating Temperature	0°C to +70°C
Storage Temperature	-40°C to 70°C
Soldering Temperature	260°C for 10 seconds

* This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

DC CHARACTERISTICS $(t_A=0^\circ\text{C to }70^\circ\text{C}; V_{CC}=5\text{V} \pm 10\%)$

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Input Low Voltage	V_{IL}	-0.3		0.8	V	1
Input High Voltage	V_{IH1}	2.0		$V_{CC}+0.3$	V	1
Input High Voltage (RST, XTAL1, PROG)	V_{IH2}	3.5		$V_{CC}+0.3$	V	1
Output Low Voltage @ $I_{OL}=1.6\text{ mA}$ (Ports 1, 2, 3)	V_{OL1}		0.15	0.45	V	
Output Low Voltage @ $I_{OL}=3.2\text{ mA}$ (Port 0, ALE, PSEN, PF, BA15-0, BD7-0, R/W, CE1N, CE1-4, PE1-4)	V_{OL2}		0.15	0.45	V	1
Output High Voltage @ $I_{OH}=-80\text{ mA}$ (Ports 1, 2, 3)	V_{OH1}	2.4	4.8		V	1
Output High Voltage @ $I_{OH}=-400\text{ }\mu\text{A}$ (Ports 0, ALE, PSEN, PF, BA15-0, BD7-0, R/W, CE1N, CE1-4, PE1-4)	V_{OH2}	2.4	4.8		V	1
Input Low Current $V_{IN}=0.45\text{V}$ (Ports 1, 2, 3)	I_{IL}			-50	μA	
Transition Current; 1 to 0 $V_{IN}=2.0\text{V}$ (Ports 1, 2, 3)	I_{TL}			-500	μA	

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DC CHARACTERISTICS (cont'd)

 $(t_A=0^{\circ}\text{C to }70^{\circ}\text{C}; V_{CC}=5\text{V} \pm 10\%)$

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Input Leakage Current $0.45 < V_{IN}, V_{CC}$ (Port 0, MSEL)	I_{IL}			± 10	μA	
RST Pulldown Resistor	R_{RE}	40		150	$\text{K}\Omega$	
VRST Pullup Resistor	R_{VR}		4.7		$\text{K}\Omega$	
PROG Pullup Resistor	R_{PR}		40		$\text{K}\Omega$	
Power Fail Warning Voltage	V_{PRW}	4.25	4.37	4.50	V	1
Minimum Operating Voltage	V_{CCMIN}	4.00	4.12	4.25	V	1
Lithium Supply Voltage	V_{IL}	2.5		4.0	V	1
Operating Current	I_{CC}			36	mA	2
Idle Mode Current	I_{IDLE}			7.0	mA	3
Stop Mode Current	I_{STOP}			80	μA	4
Pin Capacitance	C_{IN}			10	pF	5
Output Supply Voltage (V_{CCO})	V_{CCO1}			$V_{CC}-0.3$	V	1, 2
Output Supply Battery-backed Mode (V_{CCO} , CE1-4, PE1-2)	V_{CCO2}			$V_{L1}-0.55$	V	1, 8
Output Supply Current @ $V_{CCO}=V_{CC}-0.3\text{V}$	I_{CCO1}			75	mA	6
Lithium-backed Quiescent Current	I_{LI}		5	75	nA	7
Reset Trip Point in Stop Mode w/BAT=3.0V w/BAT=3.3V		4.0 4.4		4.25 4.65		1

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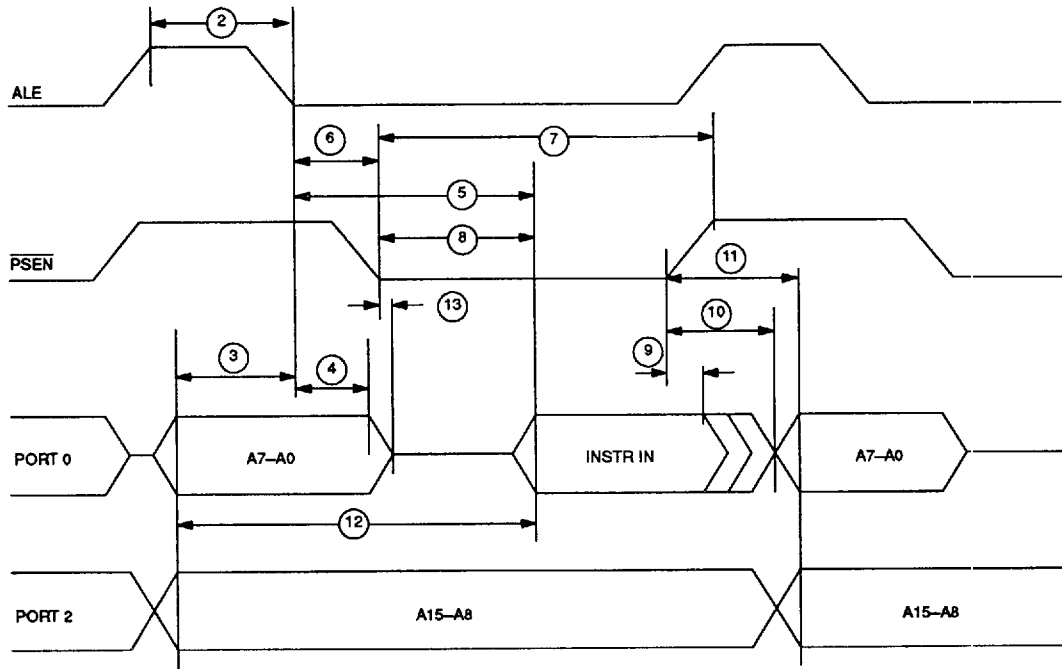
AC CHARACTERISTICS

EXPANDED BUS MODE TIMING SPECIFICATIONS

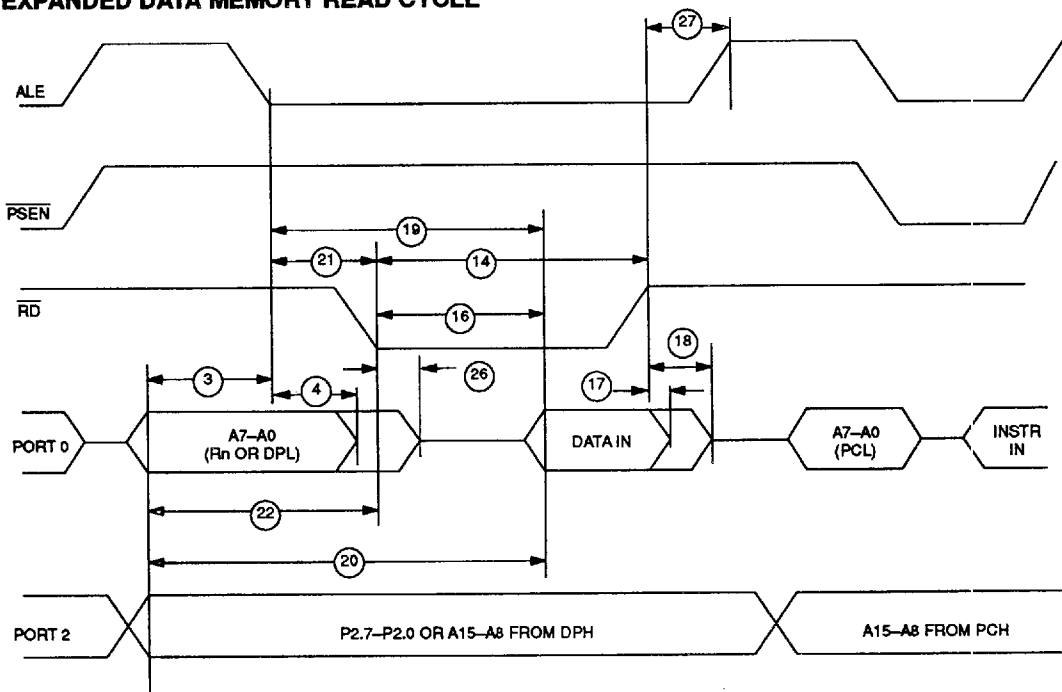
 $(t_A=0^\circ\text{C to }70^\circ\text{C}; V_{CC}=5\text{V} \pm 10\%)$

#	PARAMETER	SYMBOL	MIN	MAX	UNITS
1	Oscillator Frequency	$1/t_{CLK}$	1.0	12 (-12) 16 (-16)	MHz
2	ALE Pulse Width	t_{ALPW}	$2t_{CLK}-40$		ns
3	Address Valid to ALE Low	t_{AVALL}	$t_{CLK}-40$		ns
4	Address Hold After ALE Low	t_{AVAAV}	$t_{CLK}-35$		ns
5	ALE Low to Valid Instr. In @12 MHz @16 MHz	t_{ALLVI}		$4t_{CLK}-150$ $4t_{CLK}-90$	ns
6	ALE Low to $\overline{\text{PSEN}}$ Low	t_{ALLPSL}	$t_{CLK}-25$		ns
7	$\overline{\text{PSEN}}$ Pulse Width	t_{PSPW}	$3t_{CLK}-35$		ns
8	$\overline{\text{PSEN}}$ Low to Valid Instr. In @12 MHz @16 MHz	t_{PSLVI}		$3t_{CLK}-150$ $3t_{CLK}-90$	ns ns
9	Input Instr. Hold after $\overline{\text{PSEN}}$ Going High	t_{PSIV}	0		ns
10	Input Instr. Float after $\overline{\text{PSEN}}$ Going High	t_{PSIX}		$t_{CLK}-20$	ns
11	Address Hold after $\overline{\text{PSEN}}$ Going High	t_{PSAV}	$t_{CLK}-8$		ns
12	Address Valid to Valid Instr. In @12 MHz @16 MHz	t_{AVVI}		$5t_{CLK}-150$ $5t_{CLK}-90$	ns ns
13	$\overline{\text{PSEN}}$ Low to Address Float	t_{PSLAZ}	0		ns
14	$\overline{\text{RD}}$ Pulse Width	t_{RDPW}	$6t_{CLK}-100$		ns
15	$\overline{\text{WR}}$ Pulse Width	t_{WRPW}	$6t_{CLK}-100$		ns
16	$\overline{\text{RD}}$ Low to Valid Data In @12 MHz @16 MHz	t_{RDLDV}		$5t_{CLK}-165$ $5t_{CLK}-105$	ns ns
17	Data Hold after $\overline{\text{RD}}$ High	t_{RDHDV}	0		ns
18	Data Float after $\overline{\text{RD}}$ High	t_{RDHDZ}		$2t_{CLK}-70$	ns
19	ALE Low to Valid Data In @12 MHz @16 MHz	t_{ALLVD}		$8t_{CLK}-150$ $8t_{CLK}-90$	ns ns
20	Valid Addr. to Valid Data In @12 MHz @16 MHz	t_{AVDV}		$9t_{CLK}-165$ $9t_{CLK}-105$	ns ns
21	ALE Low to $\overline{\text{RD}}$ or $\overline{\text{WR}}$ Low	t_{ALLRDL}	$3t_{CLK}-50$	$3t_{CLK}+50$	ns
22	Address Valid to $\overline{\text{RD}}$ or $\overline{\text{WR}}$ Low	t_{AVRDL}	$4t_{CLK}-130$		ns
23	Data Valid to $\overline{\text{WR}}$ Going Low	t_{DVWRL}	$t_{CLK}-60$		ns
24	Data Valid to $\overline{\text{WR}}$ High @12 MHz @16 MHz	t_{DVWRH}	$7t_{CLK}-150$ $7t_{CLK}-90$		ns ns
25	Data Valid after $\overline{\text{WR}}$ High	t_{WRHDV}	$t_{CLK}-50$		ns
26	$\overline{\text{RD}}$ Low to Address Float	t_{RDLAZ}		0	ns
27	$\overline{\text{RD}}$ or $\overline{\text{WR}}$ High to ALE High	t_{RDHALH}	$t_{CLK}-40$	$t_{CLK}+50$	ns

EXPANDED PROGRAM MEMORY READ CYCLE

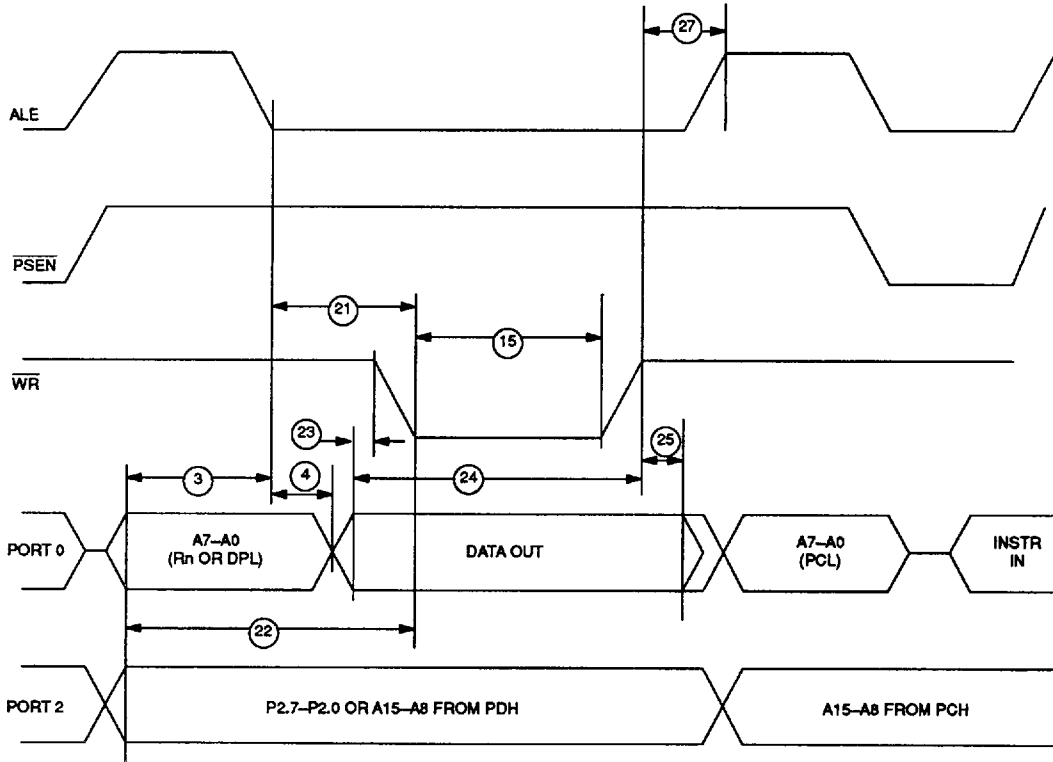


EXPANDED DATA MEMORY READ CYCLE



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EXPANDED DATA MEMORY WRITE CYCLE



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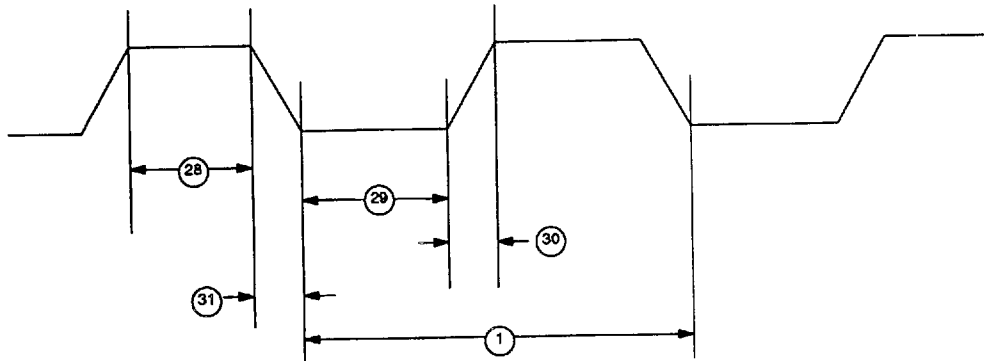
AC CHARACTERISTICS (cont'd)

EXTERNAL CLOCK DRIVE

 $(t_A = 0^\circ\text{C to } 70^\circ\text{C}; V_{CC} = 5\text{V} \pm 10\%)$

#	PARAMETER	SYMBOL	MIN	MAX	UNITS
28	External Clock High Time @16 MHz	t_{CLKHPW}	20 15		ns ns
29	External Clock Low Time @16 MHz	t_{CLKLPW}	20 15		ns ns
30	External Clock Rise Time @16 MHz	t_{CLKR}		20 15	ns ns
31	External Clock Fall Time @16 MHz	t_{CLKF}		20 15	ns ns

EXTERNAL CLOCK TIMING



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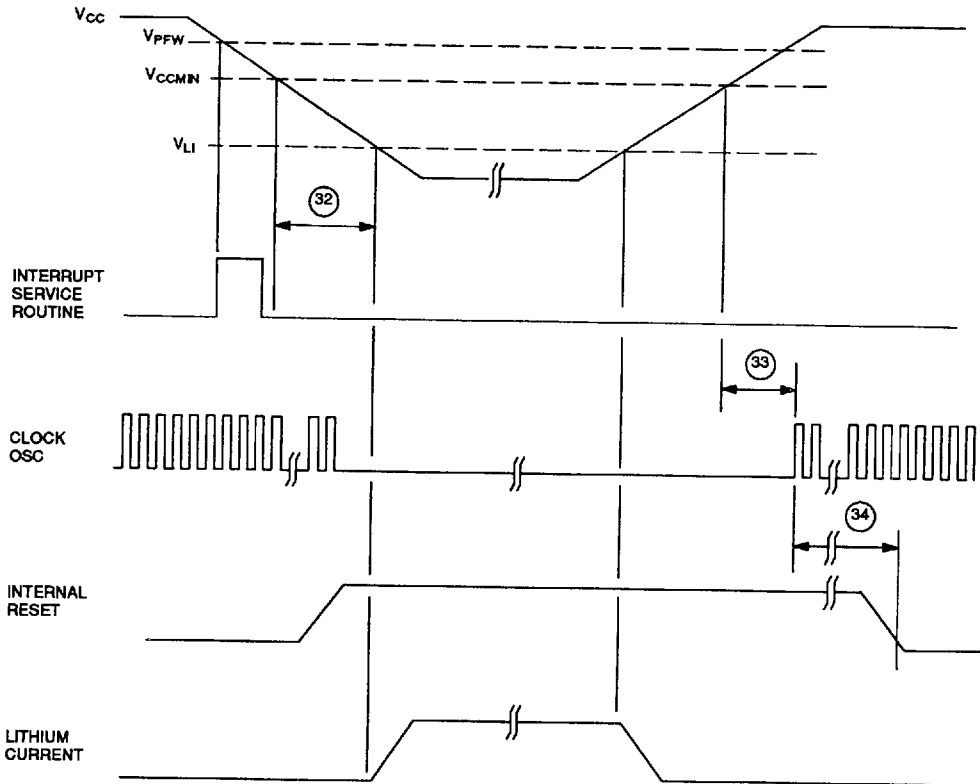
AC CHARACTERISTICS (cont'd)

POWER CYCLING TIMING

($t_A = 0^\circ\text{C to } 70^\circ\text{C}; V_{CC} = 5V \pm 10\%$)

#	PARAMETER	SYMBOL	MIN	MAX	UNITS
32	Slew Rate from V_{CCmin} to V_{LI}	t_F	130		μs
33	Crystal Start up Time	t_{CSU}		(note 9)	
34	Power On Reset Delay	t_{POR}		21504	t_{CLK}

POWER CYCLE TIMING



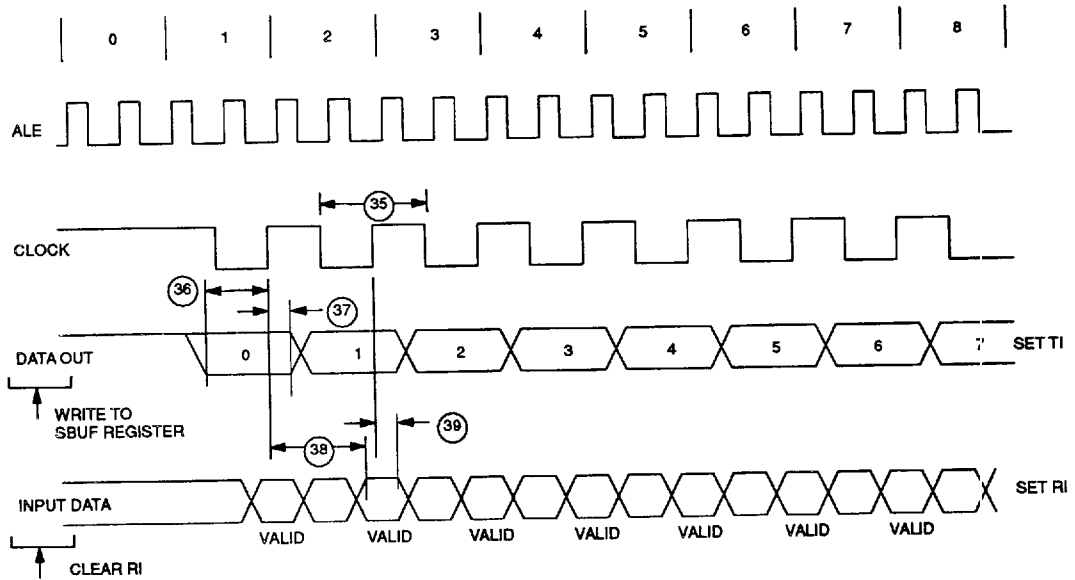
DALLAS SEMICONDUCTOR CORP

AC CHARACTERISTICS (cont'd)
SERIAL PORT TIMING – MODE 0

($t_A = 0^\circ\text{C}$ to 70°C ; $V_{CC} = 5V \pm 10\%$)

#	PARAMETER	SYMBOL	MIN	MAX	UNITS
35	Serial Port Clock Cycle Time	t_{SPCLK}	$12t_{CLK}$		μs
36	Output Data Setup to Rising Clock Edge	t_{DOCH}	$10t_{CLK} - 133$		ns
37	Output Data Hold after Rising Clock Edge	t_{CHDO}	$2t_{CLK} - 117$		ns
38	Clock Rising Edge to Input Data Valid	t_{CHDV}		$10t_{CLK} - 133$	ns
39	Input Data Hold after Rising Clock Edge	t_{CHDIV}	0		ns

SERIAL PORT TIMING – MODE 0



DALLAS SEMICONDUCTOR CORP

AC CHARACTERISTICS

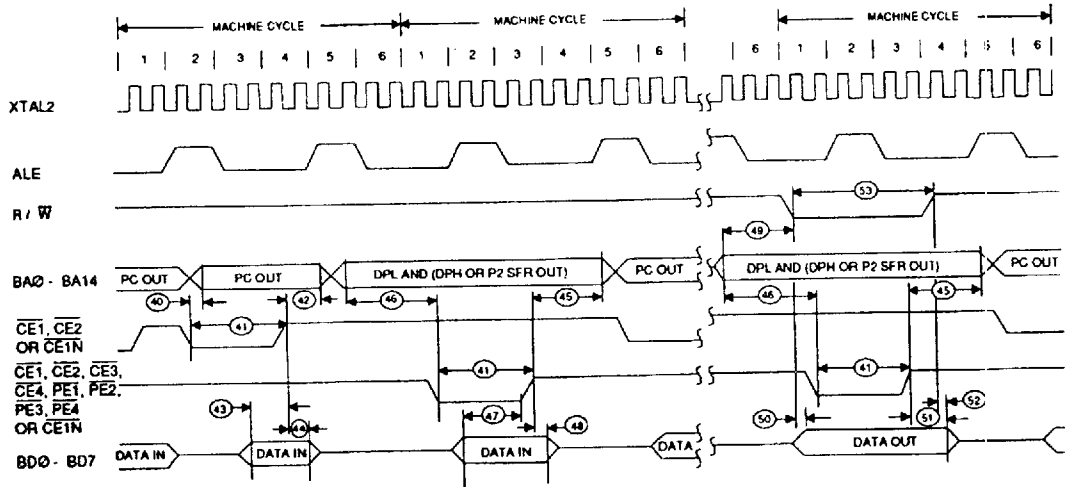
BYTEWIDE ADDRESS/DATA BUS TIMING

 $(t_A = 0^\circ\text{C to } 70^\circ\text{C}; V_{CC} = 5V \pm 10\%)$

#	PARAMETER	SYMBOL	MIN	MAX	UNITS
40	Delay to Byte-wide Address Valid from $\overline{\text{CE1}}$, $\overline{\text{CE2}}$ or $\overline{\text{CE1N}}$ Low During Opcode Fetch	t_{CE1LPA}		30	ns
41	Pulse Width of $\overline{\text{CE1-4}}$, $\overline{\text{PE1-4}}$ or $\overline{\text{CE1N}}$	t_{CEPW}	$4t_{\text{CLK}}-35$		ns
42	Byte-wide Address Hold After $\overline{\text{CE1}}$, $\overline{\text{CE2}}$ or $\overline{\text{CE1N}}$ High During Opcode Fetch	t_{CE1HPA}	$2t_{\text{CLK}}-20$		ns
43	Byte-wide Data Setup to $\overline{\text{CE1}}$, $\overline{\text{CE2}}$ or $\overline{\text{CE1N}}$ High During Opcode Fetch	t_{OVCE1H}	$1t_{\text{CLK}}+40$		ns
44	Byte-wide Data Hold After $\overline{\text{CE1}}$, $\overline{\text{CE2}}$ or $\overline{\text{CE1N}}$ High During Opcode Fetch	t_{CE1HOV}	10		ns
45	Byte-wide Address Hold After $\overline{\text{CE1-4}}$, $\overline{\text{PE1-4}}$, or $\overline{\text{CE1N}}$ High During MOVX	t_{CEHDA}	$4t_{\text{CLK}}-30$		ns
46	Delay from Byte-wide Address Valid $\overline{\text{CE1-4}}$, $\overline{\text{PE1-4}}$, or $\overline{\text{CE1N}}$ Low During MOVX	t_{CELDA}	$4t_{\text{CLK}}-35$		ns
47	Byte-wide Data Setup to $\overline{\text{CE1-4}}$, $\overline{\text{PE1-4}}$, or $\overline{\text{CE1N}}$ High During MOVX (read)	t_{DACEH}	$1t_{\text{CLK}}+40$		ns
48	Byte-wide Data Hold After $\overline{\text{CE1-4}}$, $\overline{\text{PE1-4}}$, or $\overline{\text{CE1N}}$ High During MOVX (read)	t_{CEHDV}	10		ns
49	Byte-wide Address Valid to $\overline{\text{R/W}}$ Active During MOVX (write)	t_{AVRWL}	$3t_{\text{CLK}}-35$		ns
50	Delay from $\overline{\text{R/W}}$ Low to Valid Data Out During MOVX (write)	t_{RWLDV}	20		ns
51	Valid Data Out Hold Time from $\overline{\text{CE1-4}}$, $\overline{\text{PE1-4}}$, or $\overline{\text{CE1N}}$ High	t_{CEHDV}	$1t_{\text{CLK}}-15$		ns
52	Valid Data Out Hold Time from $\overline{\text{R/W}}$ High	t_{RWHDV}	0		ns
53	Write Pulse Width ($\overline{\text{R/W}}$ Low Time)	t_{RWLPW}	$6t_{\text{CLK}}-20$		ns

DALLAS SEMICONDUCTOR CORP

BYTEWISE BUS TIMING



RPC AC CHARACTERISTICS - DBB READ

 $(t_A = 0^\circ\text{C to } 70^\circ\text{C}; V_{CC} = 5V \pm 10\%)$

#	PARAMETER	SYMBOL	MIN	MAX	UNITS
54	\overline{CS} , A_0 Setup to \overline{RD}	t_{AR}	0		ns
55	\overline{CS} , A_0 Hold After \overline{RD}	t_{RA}	0		ns
56	\overline{RD} Pulse Width	t_{RR}	160		ns
57	\overline{CS} , A_0 to Data Out Delay	t_{AD}		130	ns
58	\overline{RD} to Data Out Delay	t_{RD}	0	130	ns
59	\overline{RD} to Data Float Delay	t_{RDZ}		85	ns

RPC AC CHARACTERISTICS – DBB WRITE $(t_A = 0^\circ\text{C to }70^\circ\text{C}; V_{CC} = 5V \pm 10\%)$

#	PARAMETER	SYMBOL	MIN	MAX	UNITS
60	\overline{CS} , A_0 Setup to \overline{WR}	t_{AW}	0		ns
61A	\overline{CS} , Hold After \overline{WR}	t_{WA}	0		ns
61B	A_0 , Hold After \overline{WR}	t_{WA}	20		ns
62	\overline{WR} Pulse Width	t_{WW}	160		ns
63	Data Setup to \overline{WR}	t_{DW}	130		ns
64	Data Hold After \overline{WR}	t_{WD}	20		ns

AC CHARACTERISTICS – DMA $(t_A = 0^\circ\text{C to }70^\circ\text{C}; V_{CC} = 5V \pm 10\%)$

#	PARAMETER	SYMBOL	MIN	MAX	UNITS
65	\overline{DACK} to \overline{WR} or \overline{RD}	t_{ACC}	0		ns
66	\overline{RD} or \overline{WR} to \overline{DACK}	t_{CAC}	0		ns
67	\overline{DACK} to Data Valid	t_{ACD}	0	130	ns
68	\overline{RD} or \overline{WR} to \overline{DRQ} Cleared	t_{CRO}		110	ns

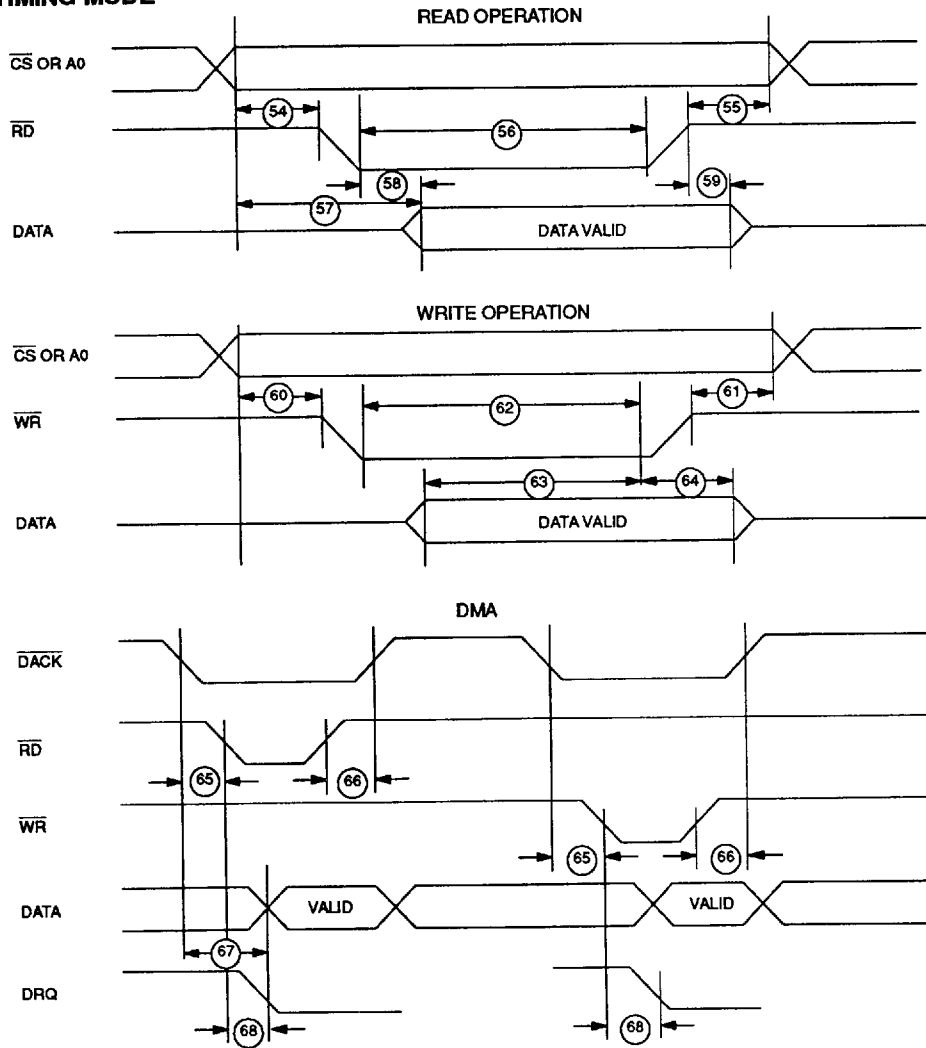
AC CHARACTERISTICS – PROG $(t_A = 0^\circ\text{C to }70^\circ\text{C}; V_{CC} = 5V \pm 10\%)$

#	PARAMETER	SYMBOL	MIN	MAX	UNITS
69	PROG Low to Active	t_{PRA}	48		CLKS
70	PROG High to Inactive	t_{PRI}	48		CLKS

DALLAS SEMICONDUCTOR CORP

DALLAS SEMICONDUCTOR CORP

RPC TIMING MODE



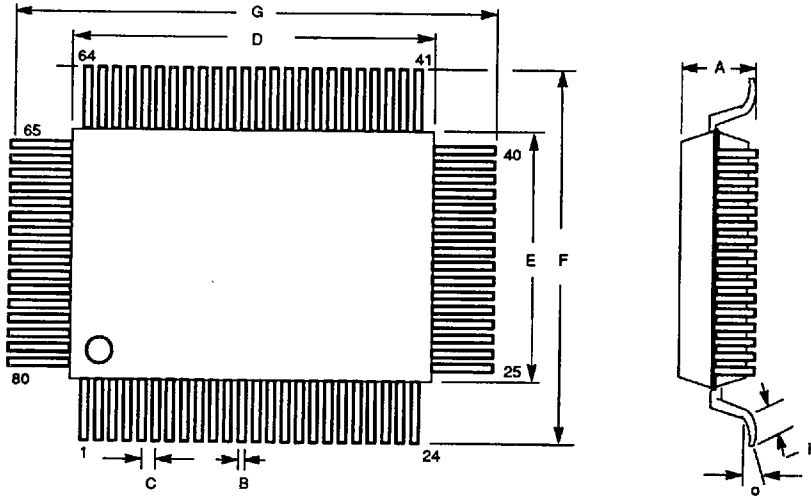
NOTES:

1. All voltages are referenced to ground.
2. Maximum operating I_{CC} is measured with all output pins disconnected; XTAL1 driven with t_{CLKR} , $t_{CLKF} = 10$ ns, $V_{IL} = 0.5V$; XTAL2 disconnected; RST = PORT0 = V_{CC} , MSEL = V_{SS} .
3. Idle mode I_{IDLE} is measured with all output pins disconnected; XTAL1 driven with t_{CLKR} , $t_{CLKF} = 10$ ns, $V_{IL} = 0.5V$; XTAL2 disconnected; PORT0 = V_{CC} , RST = MSEL = V_{SS} .
4. Stop mode I_{STOP} is measured with all output pins disconnected; PORT0 = V_{CC} ; XTAL2 not connected; RST = MSEL = XTAL1 = V_{SS} .
5. Pin Capacitance is measured with a test frequency – 1 MHz, $t_A = 25^\circ C$.

DALLAS SEMICONDUCTOR CORP

6. I_{CCO1} is the maximum average operating current that can be drawn from V_{CCO} in normal operation.
7. I_{L1} is the current drawn from V_{L1} input when $V_{CC} = 0V$ and V_{CCO} is disconnected.
8. V_{CCO2} is measured with $V_{CC} < V_{L1}$, and a maximum load of $10 \mu A$ on V_{CCO} .
9. Crystal start-up time is the time required to get the mass of the crystal into vibrational motion from the time that power is first applied to the circuit until the first clock pulse is produced by the on-chip oscillator. The user should check with the crystal vendor for a worst case specification on this time.

DS5001FP CMOS MICROCONTROLLER



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	-	2.91	3.15
B	0.25	0.35	0.45
C	-	0.80	-
D	19.85	20.00	20.15
E	13.85	14.00	14.15
F	17.40	17.86	18.20
G	23.40	23.86	24.20
H	0.40	-	1.3
I	0	-	10°